

[METHOD FOR REDUCING AMINE BASED CONTAMINANTS]

Abstract

A method for reducing resist poisoning is provided. The method includes forming a first structure in a dielectric on a substrate and reducing amine related contaminants from the dielectric and the substrate created after the formation of the first structure. The method further includes forming a second structure in the dielectric. A first organic film may be formed on the substrate which is then heated and removed from the substrate to reduce the contaminant. Alternatively, a plasma treatment or cap may be provided. A second organic film is formed on the substrate and patterned to define a second structure in the dielectric.